

NANYANG TECHNOLOGICAL UNIVERSITY  
SCHOOL OF ELECTRICAL & ELECTRONIC ENGINEERING  
EE4341/EE6341 ADVANCED ANALOG CIRCUITS  
TUTORIAL 7

1. Fig. 1 shows a Class AB power amplifier biased by a constant current source  $I_{\text{bias}} = 5$  mA. The load  $R_L = 100 \, \Omega$  and the transistor and the diode parameters are:  $I_S = 10^{-13}$  A and  $V_T = 26$  mV. Current gains  $\beta_n = 100$  and  $\beta_p = 20$  for npn and pnp transistors, respectively.
  - (a) Determine  $V_{BB}$ ,  $I_C$  and  $V_{BE}$  for each transistor when  $v_o = 0$ .
  - (b) Repeat part (a) when  $v_o = +10$  V.
  - (c) What is the instantaneous powers delivered to the load and dissipated in each transistor when  $v_o = +10$  V?

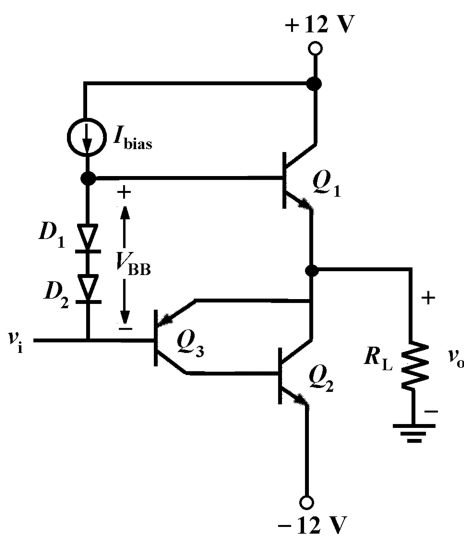


Figure 1

2. Fig. 2 shows a Class D power amplifier to drive a load  $R_L = 8 \Omega$ . Assume  $V_{CE(sat)} = 0.3$  V and the LC low pass filter is lossless.
  - (a) What is the maximum power that can be delivered to the load?
  - (b) If each switching transition of the transistor is about 5% of the period of switching frequency, what is the conversion efficiency at maximum output power?
  - (c) Repeat part (b) if faster transistors are used with the switching transition reduced to 2.5%.

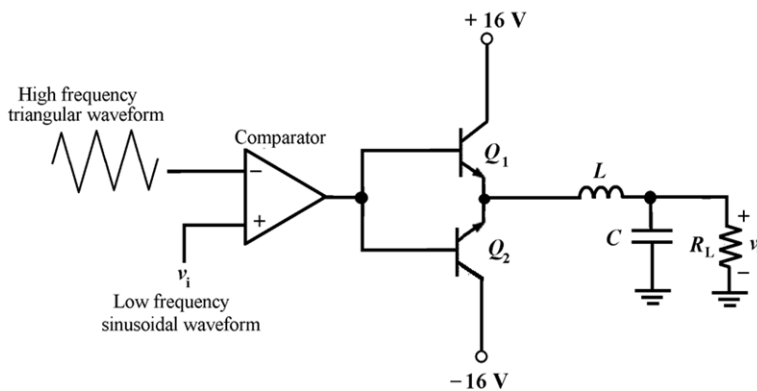


Figure 2

3. The maximum permissible junction temperature of a power transistor is  $150^{\circ}\text{C}$ . It is desired to operate the transistor with a power dissipation of  $15\text{ W}$  in an ambient temperature of  $40^{\circ}\text{C}$ . The thermal resistances of the transistor:  $\theta_{JC} = 0.5^{\circ}\text{C/W}$  (junction to case) and  $\theta_{CA} = 10^{\circ}\text{C/W}$  (case to ambient).
- (a) Determine whether a heat sink is required for this application.
  - (b) If a heat sink is needed, determine the required thermal resistance. To mount the heat sink, there is a mica washer between the transistor case and the heat sink. The thermal resistance of the mica washer  $\theta_W = 0.5^{\circ}\text{C/W}$ .